

## AMENDMENT

### Claim Amendments

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (currently amended) A method of forming a continuous isolation region of controlled doping level in a substrate below an active region of ~~controlling the breakdown voltage of~~ a snapback device, comprising  
~~controlling doping levels of an isolation region by~~ using a perforated mask with multiple perforations during doping of the isolation region.
11. (original) A method of claim 10, further comprising annealing the device.
12. (original) A method of claim 10, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.
13. (currently amended) A method of increasing the breakdown voltage of a snapback device comprising  
forming an isolation layer in a ~~between active regions and~~ substrate of the said snapback device, and

thereafter forming an active region above the isolation layer, wherein forming the isolation layer includes forming spotted implants and causing the spotted implants substantially to combine to form said isolation region.

14. (original) A method of claim 13, wherein the spotted implants are formed by making use of a mask with intermittent openings.
15. (original) A method of claim 13, wherein the spotted implants are provided before one or both of an epitaxial layer being grown and high diffusion drive taking place.
16. (original) A method of claim 13, wherein the snapback device is an ESD protection device.
17. (original) A method of claim 13, further comprising annealing the device.
18. (original) A method of claim 13, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.